Appendix - Specification
Marked to Show Changes

One feature of an embodiment of the device package 120 and the conductive member 130 described above with reference to Figures 2-4 is that the dielectric material 160 adjacent to the conductive portions 131 can be selected to control capacitive coupling between neighboring conductive portions 131. For example, in one embodiment, the dielectric material 160 can include Teflon™ (polytetrafluoroethylene) and can have a dielectric constant of from approximately 1.0 to approximately 2.0. Accordingly, the likelihood for capacitive coupling between neighboring conductive portions 131 can be reduced when compared to conventional arrangements (such as the arrangement described above with reference to Figure 1) that have relatively high dielectric encapsulating materials positioned between adjacent leadfingers. In other embodiments, the dielectric material 160 can have a dielectric constant higher than 2.0, but less than the dielectric constant of conventional encapsulating materials, which is approximately 3.5 and above.

Appendix - Claims
Marked to Show Changes

12. (Amended) The method of claim 1, further comprising selecting the dielectric material to include polytetrafluoroethyleneTeflon™.

16. (Amended) The method of claim 13, further comprising selecting the dielectric material to include gas, argon and/or helium.

20. (Amended) The method of claim 1413 wherein disposing the dielectric material includes disposing the dielectric material in liquid or vapor phase.

29. (Amended) A method for packaging a microelectronic substrate, comprising:

positioning leadfingers of a leadframe adjacent to corresponding bond sites of the microelectronic substrate;

electrically coupling the leadfingers to the bond sites;

disposing a first dielectric material adjacent to first surfaces of the leadfingers and the microelectronic substrate;

disposing a second dielectric material adjacent to second surfaces of the leadfingers facing opposite the first surfaces; and

introducing at least some of the first and/or second dielectric material into a gap between adjacent leadfingers by biasing the leadframe toward the microelectronic substrate and/or applying heat to at least one of the dielectric materials wherein at least one of the first and second the dielectric materials has a dielectric constant less than about 3.5.